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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	221
Number of Gates	300000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	324-BGA
Supplier Device Package	324-FBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000l-fgg324i

Email: info@E-XFL.COM

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FPGA Array Architecture in Low Power Flash Devices



Note: Flash\*Freeze technology only applies to IGLOOe devices.

Figure 1-7 • IGLOOe and ProASIC3E Device Architecture Overview (AGLE600 device is shown)

### I/O State of Newly Shipped Devices

Devices are shipped from the factory with a test design in the device. The power-on switch for VCC is OFF by default in this test design, so I/Os are tristated by default. Tristated means the I/O is not actively driven and floats. The exact value cannot be guaranteed when it is floating. Even in simulation software, a tristate value is marked as unknown. Due to process variations and shifts, tristated I/Os may float toward High or Low, depending on the particular device and leakage level.

If there is concern regarding the exact state of unused I/Os, weak pull-up/pull-down should be added to the floating I/Os so their state is controlled and stabilized.

# 2 – Flash\*Freeze Technology and Low Power Modes

### Flash\*Freeze Technology and Low Power Modes

Microsemi IGLOO,<sup>®</sup> IGLOO nano, IGLOO PLUS, ProASIC<sup>®</sup>3L, and Radiation-Tolerant (RT) ProASIC3 FPGAs with Flash\*Freeze technology are designed to meet the most demanding power and area challenges of today's portable electronics products with a reprogrammable, small-footprint, full-featured flash FPGA. These devices offer lower power consumption in static and dynamic modes, utilizing the unique Flash\*Freeze technology, than any other FPGA or CPLD.

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 devices offer various power-saving modes that enable every system to utilize modes that achieve the lowest total system power. Low Power Active capability (static idle) allows for ultra-low power consumption while the device is operational in the system by maintaining SRAM, registers, I/Os, and logic functions.

Flash\*Freeze technology provides an ultra-low power static mode (Flash\*Freeze mode) that retains all SRAM and register information with rapid recovery to Active (operating) mode. IGLOO nano and IGLOO PLUS devices have an additional feature when operating in Flash\*Freeze mode, allowing them to retain I/O states as well as SRAM and register states. This mechanism enables the user to quickly (within 1  $\mu$ s) enter and exit Flash\*Freeze mode by activating the Flash\*Freeze (FF) pin while all power supplies are kept in their original states. In addition, I/Os and clocks connected to the FPGA can still be toggled without impact on device power consumption. While in Flash\*Freeze mode, the device retains all core register states and SRAM information. This mode can be configured so that no power is consumed by the I/O banks, clocks, JTAG pins, or PLLs; and the IGLOO and IGLOO PLUS devices consume as little as 5  $\mu$ W, while IGLOO nano devices consume as little as 2  $\mu$ W. Microsemi offers a state management IP core to aid users in gating clocks and managing data before entering Flash\*Freeze mode.

This document will guide users in selecting the best low power mode for their applications, and introduces Microsemi's Flash\*Freeze management IP core.



Figure 2-1 shows the concept of FF pin control in Flash\*Freeze mode type 1.



Figure 2-2 shows the timing diagram for entering and exiting Flash\*Freeze mode type 1.



Figure 2-2 • Flash\*Freeze Mode Type 1 – Timing Diagram

ProASIC3L FPGA Fabric User's Guide

Date	Changes	Page
v2.1 (October 2008)	The title changed from "Flash*Freeze Technology and Low Power Modes in IGLOO, IGLOO PLUS, and ProASIC3L Devices" to Actel's Flash*Freeze Technology and Low Power Modes."	N/A
	The "Flash Families Support the Flash*Freeze Feature" section was updated.	22
	Significant changes were made to this document to support Libero IDE v8.4 and later functionality. RT ProASIC3 device support information is new. In addition to the other major changes, the following tables and figures were updated or are new: Figure 2-3 • Flash*Freeze Mode Type 2 – Controlled by Flash*Freeze Pin and	
	Internal Logic (LSICC signal) – updated Figure 2-5 • Narrow Clock Pulses During Flash*Freeze Entrance and Exit – new	27
	Figure 2-10 • Flash*Freeze Management IP Block Diagram – new	30
	Figure 2-11 • FSM State Diagram – new	37
	Table 2-6 • IGLOO nano and IGLOO PLUS Flash*Freeze Mode (type 1 and type 2)—I/O Pad State – updated	38 29
	Please review the entire document carefully.	20
v1.3 (June 2008)	The family description for ProASIC3L in Table 2-1 • Flash-Based FPGAs was updated to include 1.5 V.	22
v1.2 (March 2008)	The part number for this document was changed from 51700094-003-1 to 51700094-004-2.	N/A
	The title of the document was changed to "Flash*Freeze Technology and Low Power Modes in IGLOO, IGLOO PLUS, and ProASIC3L Devices."	N/A
	The "Flash*Freeze Technology and Low Power Modes" section was updated to remove the parenthetical phrase, "from 25 $\mu$ W," in the second paragraph. The following sentence was added to the third paragraph: "IGLOO PLUS has an additional feature when operating in Flash*Freeze mode, allowing it to retain I/O states as well as SRAM and register states."	21
	The "Power Conservation Techniques" section was updated to add $V_{JTAG}$ to the parenthetical list of power supplies that should be tied to the ground plane if unused. Additional information was added regarding how the software configures unused I/Os.	2-1
	Table 2-1 • Flash-Based FPGAs and the accompanying text was updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	22
	The "Flash*Freeze Mode" section was revised to include that I/O states are preserved in Flash*Freeze mode for IGLOO PLUS devices. The last sentence in the second paragraph was changed to, "If the FF pin is not used, it can be used as a regular I/O." The following sentence was added for Flash*Freeze mode type 2: "Exiting the mode is controlled by either the FF pin OR the user-defined LSICC signal."	24
	The "Flash*Freeze Type 1: Control by Dedicated Flash*Freeze Pin" section was revised to change instructions for implementing this mode, including instructions for implementation with Libero IDE v8.3.	24
	Figure 2-1 • Flash*Freeze Mode Type 1 – Controlled by the Flash*Freeze Pin was updated.	25
	The "Flash*Freeze Type 2: Control by Dedicated Flash*Freeze Pin and Internal Logic" section was renamed from "Type 2 Software Implementation."	26
	The "Type 2 Software Implementation for Libero IDE v8.3" section is new.	2-6

### Simple Design Example

Consider a design consisting of six building blocks (shift registers) and targeted for an A3PE600-PQ208 (Figure 3-16 on page 68). The example design consists of two PLLs (PLL1 has GLA only; PLL2 has both GLA and GLB), a global reset (ACLR), an enable (EN\_ALL), and three external clock domains (QCLK1, QCLK2, and QCLK3) driving the different blocks of the design. Note that the PQ208 package only has two PLLs (which access the chip global network). Because of fanout, the global reset and enable signals need to be assigned to the chip global resources. There is only one free chip global for the remaining global (QCLK1, QCLK2, QCLK3). Place two of these signals on the quadrant global resource. The design example demonstrates manually assignment of QCLK1 and QCLK2 to the quadrant global using the PDC command.



Figure 3-19 • Block Diagram of the Global Management Example Design

During Layout, Designer will assign two of the signals to quadrant global locations.

#### Step 3 (optional)

You can also assign the QCLK1\_c and QCLK2\_c nets to quadrant regions using the following PDC commands:

assign\_local\_clock -net QCLK1\_c -type quadrant UL assign\_local\_clock -net QCLK2\_c -type quadrant LL

#### Step 4

Import this PDC with the netlist and run Compile again. You will see the following in the Compile report:

The fol Fanout	-	ve been assigned to a global resource: Name
1536	INT_NET	Net : EN_ALL_c Driver: EN_ALL_pad_CLKINT
1536	SET/RESET_NET	Source: AUTO PROMOTED Net : ACLR_c Driver: ACLR_pad_CLKINT
256	CLK_NET	Source: AUTO PROMOTED Net : QCLK3_c Driver: QCLK3_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : \$1N14 Driver: \$1I5/Core
256	CLK_NET	Source: ESSENTIAL Net : \$1N12 Driver: \$116/Core Source: ESSENTIAL
256	CLK_NET	Net : \$1N10 Driver: \$116/Core Source: ESSENTIAL
The fol	lowing nets ha	ve been assigned to a quadrant clock resource using PDC:
Fanout		
	CLK_NET	Net : QCLK1_c Driver: QCLK1_pad_CLKINT Region: guadrant_UL
256	CLK_NET	Net : QCLK2_c Driver: QCLK2_pad_CLKINT Region: quadrant_LL

#### Step 5

Run Layout.

### **Global Management in PLL Design**

This section describes the legal global network connections to PLLs in the low power flash devices. For detailed information on using PLLs, refer to "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" section on page 77. Microsemi recommends that you use the dedicated global pins to directly drive the reference clock input of the associated PLL for reduced propagation delays and clock distortion. However, low power flash devices offer the flexibility to connect other signals to reference clock inputs. Each PLL is associated with three global networks (Figure 3-5 on page 52). There are some limitations, such as when trying to use the global and PLL at the same time:

- If you use a PLL with only primary output, you can still use the remaining two free global networks.
- If you use three globals associated with a PLL location, you cannot use the PLL on that location.
- If the YB or YC output is used standalone, it will occupy one global, even though this signal does not go to the global network.

# **Global Buffers with PLL Function**

Clocks requiring frequency synthesis or clock adjustments can utilize the PLL core before connecting to the global / quadrant global networks. A maximum of 18 CCC global buffers can be instantiated in a device—three per CCC and up to six CCCs per device. Each PLL core can generate up to three global/quadrant clocks, while a clock delay element provides one.

The PLL functionality of the clock conditioning block is supported by the PLL macro.

Clock Source	Clock Conditioning	Output
Input LVDS/LVPECL Macro	PLL Macro	GLA or GLA and (GLB or YB) or GLA and (GLC or YC) or GLA and (GLB or YB) and (GLC or YC)

Notes:

- 1. For Fusion only.
- 2. Refer to the IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide for more information.
- 3. For INBUF\* driving a PLL macro or CLKDLY macro, the I/O will be hard-routed to the CCC; i.e., will be placed by software to a dedicated Global I/O.
- 4. IGLOO nano and ProASIC3 nano devices do not support differential inputs.

#### Figure 4-4 • CCC Options: Global Buffers with PLL

The PLL macro provides five derived clocks (three independent) from a single reference clock. The PLL macro also provides power-down input and lock output signals. The additional inputs shown on the macro are configuration settings, which are configured through the use of SmartGen. For manual setting of these bits refer to the *IGLOO*, *ProASIC3*, *SmartFusion*, *and Fusion Macro Library Guide* for details.

Figure 4-6 on page 87 illustrates the various clock output options and delay elements.

Config. Bits	Signal	Name	Description
83	RXCSEL <sup>1</sup>	CLKC input selection	Select the CLKC input clock source between RC oscillator and crystal oscillator (refer to Table 4-16 on page 110). <sup>2</sup>
82	RXBSEL <sup>1</sup>	CLKB input selection	Select the CLKB input clock source between RC oscillator and crystal oscillator (refer to Table 4-16 on page 110). <sup>2</sup>
81	RXASEL <sup>1</sup>	CLKA input selection	Select the CLKA input clock source between RC oscillator and crystal oscillator (refer to Table 4-16 on page 110). <sup>2</sup>
80	RESETEN	Reset Enable	Enables (active high) the synchronization of PLL output dividers after dynamic reconfiguration (SUPDATE). The Reset Enable signal is READ-ONLY.
79	DYNCSEL	Clock Input C Dynamic Select	Configures clock input C to be sent to GLC for dynamic control. <sup>2</sup>
78	DYNBSEL	Clock Input B Dynamic Select	Configures clock input B to be sent to GLB for dynamic control. <sup>2</sup>
77	DYNASEL	Clock Input A Dynamic Select	Configures clock input A for dynamic PLL configuration. <sup>2</sup>
<76:74>	VCOSEL[2:0]	VCO Gear Control	Three-bit VCO Gear Control for four frequency ranges (refer to Table 4-19 on page 111 and Table 4-20 on page 111).
73	STATCSEL	MUX Select on Input C	MUX selection for clock input C <sup>2</sup>
72	STATBSEL	MUX Select on Input B	MUX selection for clock input B <sup>2</sup>
71	STATASEL	MUX Select on Input A	MUX selection for clock input A <sup>2</sup>
<70:66>	DLYC[4:0]	YC Output Delay	Sets the output delay value for YC.
<65:61>	DLYB[4:0]	YB Output Delay	Sets the output delay value for YB.
<60:56>	DLYGLC[4:0]	GLC Output Delay	Sets the output delay value for GLC.
<55:51>	DLYGLB[4:0]	GLB Output Delay	Sets the output delay value for GLB.
<50:46>	DLYGLA[4:0]	Primary Output Delay	Primary GLA output delay
45	XDLYSEL	System Delay Select	When selected, inserts System Delay in the feedback path in Figure 4-20 on page 101.
<44:40>	FBDLY[4:0]	Feedback Delay	Sets the feedback delay value for the feedback element in Figure 4-20 on page 101.
<39:38>	FBSEL[1:0]	Primary Feedback Delay Select	Controls the feedback MUX: no delay, include programmable delay element, or use external feedback.
<37:35>	OCMUX[2:0]	Secondary 2 Output Select	Selects from the VCO's four phase outputs for GLC/YC.
<34:32>	OBMUX[2:0]	Secondary 1 Output Select	Selects from the VCO's four phase outputs for GLB/YB.

#### Table 4-8 • Configuration Bit Descriptions for the CCC Blocks (continued)

Notes:

1. The <88:81> configuration bits are only for the Fusion dynamic CCC.

 This value depends on the input clock source, so Layout must complete before these bits can be set. After completing Layout in Designer, generate the "CCC\_Configuration" report by choosing Tools > Report > CCC\_Configuration. The report contains the appropriate settings for these bits.

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

# **Software Configuration**

SmartGen automatically generates the desired CCC functional block by configuring the control bits, and allows the user to select two CCC modes: Static PLL and Delayed Clock (CLKDLY).

### **Static PLL Configuration**

The newly implemented Visual PLL Configuration Wizard feature provides the user a quick and easy way to configure the PLL with the desired settings (Figure 4-23). The user can invoke SmartGen to set the parameters and generate the netlist file with the appropriate flash configuration bits set for the CCCs. As mentioned in "PLL Macro Block Diagram" on page 85, the input reference clock CLKA can be configured to be driven by Hardwired I/O, External I/O, or Core Logic. The user enters the desired settings for all the parameters (output frequency, output selection, output phase adjustment, clock delay, feedback delay, and system delay). Notice that the actual values (divider values, output frequency, delay values, and phase) are shown to aid the user in reaching the desired design frequency in real time. These values are typical-case data. Best- and worst-case data can be observed through static timing analysis in SmartTime within Designer.

For dynamic configuration, the CCC parameters are defined using either the external JTAG port or an internally defined serial interface via the built-in dynamic shift register. This feature provides the ability to compensate for changes in the external environment.



Figure 4-23 • Visual PLL Configuration Wizard

# **SRAM and FIFO Architecture**

To meet the needs of high-performance designs, the memory blocks operate strictly in synchronous mode for both read and write operations. The read and write clocks are completely independent, and each can operate at any desired frequency up to 250 MHz.

- 4k×1, 2k×2, 1k×4, 512×9 (dual-port RAM—2 read / 2 write or 1 read / 1 write)
- 512×9, 256×18 (2-port RAM—1 read / 1 write)
- Sync write, sync pipelined / nonpipelined read

Automotive ProASIC3 devices support single-port SRAM capabilities or dual-port SRAM only under specific conditions. Dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). The Libero SoC software macro libraries support a dual-port macro only. For use of this macro as a single-port SRAM, the inputs and clock of one port should be tied off (grounded) to prevent errors during design compile. For use in dual-port mode, the same clock with an inversion between the two clock pins of the macro should be used in the design to prevent errors during compile.

The memory block includes dedicated FIFO control logic to generate internal addresses and external flag logic (FULL, EMPTY, AFULL, AEMPTY).

Simultaneous dual-port read/write and write/write operations at the same address are allowed when certain timing requirements are met.

During RAM operation, addresses are sourced by the user logic, and the FIFO controller is ignored. In FIFO mode, the internal addresses are generated by the FIFO controller and routed to the RAM array by internal MUXes.

The low power flash device architecture enables the read and write sizes of RAMs to be organized independently, allowing for bus conversion. For example, the write size can be set to 256×18 and the read size to 512×9.

Both the write width and read width for the RAM blocks can be specified independently with the WW (write width) and RW (read width) pins. The different D×W configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1. When widths of one, two, or four are selected, the ninth bit is unused. For example, when writing nine-bit values and reading four-bit values, only the first four bits and the second four bits of each nine-bit value are addressable for read operations. The ninth bit is not accessible.

Conversely, when writing four-bit values and reading nine-bit values, the ninth bit of a read operation will be undefined. The RAM blocks employ little-endian byte order for read and write operations.

# **Memory Blocks and Macros**

Memory blocks can be configured with many different aspect ratios, but are generically supported in the macro libraries as one of two memory elements: RAM4K9 or RAM512X18. The RAM4K9 is configured as a true dual-port memory block, and the RAM512X18 is configured as a two-port memory block. Dual-port memory allows the RAM to both read from and write to either port independently. Two-port memory allows the RAM to read from one port and write to the other using a common clock or independent read and write clocks. If needed, the RAM4K9 blocks can be configured as two-port memory blocks. The memory block can be configured as a FIFO by combining the basic memory block with dedicated FIFO controller logic. The FIFO macro is named FIFO4KX18 (Figure 6-3 on page 152).

Clocks for the RAM blocks can be driven by the VersaNet (global resources) or by regular nets. When using local clock segments, the clock segment region that encompasses the RAM blocks can drive the RAMs. In the dual-port configuration (RAM4K9), each memory block port can be driven by either risingedge or falling-edge clocks. Each port can be driven by clocks with different edges. Though only a risingedge clock can drive the physical block itself, the Microsemi Designer software will automatically bubblepush the inversion to properly implement the falling-edge trigger for the RAM block. SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

### Example of RAM Initialization

This section of the document presents a sample design in which a 4×4 RAM block is being initialized through the JTAG port. A test feature has been implemented in the design to read back the contents of the RAM after initialization to verify the procedure.

The interface block of this example performs two major functions: initialization of the RAM block and running a test procedure to read back the contents. The clock output of the interface is either the write clock (for initialization) or the read clock (for reading back the contents). The Verilog code for the interface block is included in the "Sample Verilog Code" section on page 167.

For simulation purposes, users can declare the input ports of the UJTAG macro for easier assignment in the testbench. However, the UJTAG input ports should not be declared on the top level during synthesis. If the input ports of the UJTAG are declared during synthesis, the synthesis tool will instantiate input buffers on these ports. The input buffers on the ports will cause Compile to fail in Designer.

Figure 6-10 shows the simulation results for the initialization step of the example design.

The CLK\_OUT signal, which is the clock output of the interface block, is the inverted DR\_UPDATE output of the UJTAG macro. It is clear that it gives sufficient time (while the TAP Controller is in the Data Register Update state) for the write address and data to become stable before loading them into the RAM block.

Figure 6-11 presents the test procedure of the example. The data read back from the memory block matches the written data, thus verifying the design functionality.

Figure 6-10 • Simulation of Initialization Step

Figure 6-11 • Simulation of the Test Procedure of the Example

I/O Structures in IGLOO and ProASIC3 Devices

	Maximum Performance		
Specification	ProASIC3	IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage	IGLOO V2, 1.2 V DC Core Supply Voltage
LVTTL/LVCMOS 3.3 V	200 MHz	180 MHz	TBD
LVCMOS 2.5 V	250 MHz	230 MHz	TBD
LVCMOS 1.8 V	200 MHz	180 MHz	TBD
LVCMOS 1.5 V	130 MHz	120 MHz	TBD
PCI	200 MHz	180 MHz	TBD
PCI-X	200 MHz	180 MHz	TBD
LVDS	350 MHz	300 MHz	TBD
LVPECL	350 MHz	300 MHz	TBD

# Table 7-6 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in IGLOO and ProASIC Devices (maximum drive strength and high slew selected)

I/O Structures in IGLOOe and ProASIC3E Devices

#### Table 8-9 • Hot-Swap Level 1

Description	Cold-swap
Power Applied to Device	No
Bus State	-
Card Ground Connection	-
Device Circuitry Connected to Bus Pins	-
Example Application	System and card with Microsemi FPGA chip are powered down, and the card is plugged into the system. Then the power supplies are turned on for the system but not for the FPGA on the card.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices: Compliant Other IGLOO/ProASIC3 devices: Compliant if bus switch used to isolate FPGA I/Os from rest of system IGLOOe/ProASIC3E devices: Compliant I/Os can, but do not have to be set to hot-insertion mode.

Table 8-10 • Hot-Swap Level 2

Description	Hot-swap while reset
Power Applied to Device	Yes
Bus State	Held in reset state
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	-
Example Application	In the PCI hot-plug specification, reset control circuitry isolates the card busses until the card supplies are at their nominal operating levels and stable.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode. Other IGLOO/ProASIC3 devices: Compliant

# List of Changes

Date	Changes	Page
August 2012	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low. The title of the figures was revised from "I/O Block Logical Representation" (SAR 40685).	213, 220
	AGLE1500 was removed from Table 8-2 • Supported I/O Standards because it is not a valid offering. LVCMOS 1.2 was added to the single-ended standards. LVCMOS 1.2 was added to Table 8-3 • VCCI Voltages and Compatible IGLOOe and ProASIC3E Standards (SAR 33207).	215, 217
	Lack of a heading for the "User I/O Naming Convention" section made the information difficult to locate. A heading now introduces the user I/O naming conventions (SAR 38059).	245
	Figure 8-5 • Simplified I/O Buffer Circuitry and Table 8-8 • Programmable I/O Features (user control via I/O Attribute Editor) were modified to indicate that programmable input delay control is applicable only to ProASIC3E, IGLOOe, ProASIC3EL, and RT ProASIC3 devices (SAR 39666).	222, 227
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663).	246, 248
June 2011	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).	213, 220
	The "Pro I/Os—IGLOOe, ProASIC3EL, and ProASIC3E" section was revised. Formerly it stated, "3.3 V PCI and 3.3 V PCI-X are 5 V–tolerant." This sentence now reads, "3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant" (SAR 20983).	215
	Table 8-5 • Legal IGLOOe and ProASIC3E I/O Usage Matrix within the Same Bank was revised as follows (SAR 22467):	217
	The combination of 3.3 V I/O bank voltage with 1.50 V minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made an illegal combination (now gray instead of white).	
	The combination of 2.5 V I/O bank voltage with no minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made a valid combination (now white instead of gray).	
	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V-tolerant CMOS input buffer and a push-pull output buffer."	223
	The "Electrostatic Discharge Protection" section was revised to remove references to tolerances (refer to the <i>Reliability Report</i> for tolerances). The Machine Model (MM) is not supported and was deleted from this section (SAR 24385).	231
	The "I/O Interfacing" section was revised to state that low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected, removing "without adding any extra circuitry," which was incorrect (SAR 21404).	247
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	The terminology in the "Low Power Flash Device I/O Support" section was revised.	214

The following table lists critical changes that were made in each revision of the document.

I/O Structures in IGLOOe and ProASIC3E Devices

Date	Changes	Page
v1.3 (October 2008)	The "Low Power Flash Device I/O Support" section was revised to include new families and make the information more concise.	214
v1.2 (June 2008)	<ul> <li>The following changes were made to the family descriptions in Table 8-1 · Flash-Based FPGAs:</li> <li>ProASIC3L was updated to include 1.5 V.</li> <li>The number of PLLs for ProASIC3E was changed from five to six.</li> </ul>	214
v1.1 (March 2008)	This document was previously part of <i>I/O Structures in IGLOO and ProASIC3</i> <i>Devices.</i> To provide information specific to IGLOOe, ProASIC3E, and ProASIC3EL, the content was separated and made into a new document. For information on other low power flash family I/O structures, refer to the following documents: <i>I/O Structures in IGLOO and ProASIC3 Devices</i> contains information specific to IGLOO, ProASIC3, and ProASIC3L I/O features. <i>I/O Structures in IGLOO PLUS Devices</i> contains information specific to IGLOO PLUS I/O features.	N/A

DDR for Microsemi's Low Power Flash Devices

```
module ddr_test(DIN, CLK, CLR, DOUT);
input DIN, CLK, CLR;
output DOUT;
Inbuf_ddr Inbuf_ddr (.PAD(DIN), .CLR(clr), .CLK(clk), .QR(qr), .QF(qf));
Outbuf_ddr Outbuf_ddr (.DataR(qr),.DataF(qf), .CLR(clr), .CLK(clk),.PAD(DOUT));
INBUF INBUF_CLR (.PAD(CLR), .Y(clr));
INBUF INBUF_CLK (.PAD(CLK), .Y(clk));
```

endmodule

### **Simulation Consideration**

Microsemi DDR simulation models use inertial delay modeling by default (versus transport delay modeling). As such, pulses that are shorter than the actual gate delays should be avoided, as they will not be seen by the simulator and may be an issue in post-routed simulations. The user must be aware of the default delay modeling and must set the correct delay model in the simulator as needed.

# Conclusion

Fusion, IGLOO, and ProASIC3 devices support a wide range of DDR applications with different I/O standards and include built-in DDR macros. The powerful capabilities provided by SmartGen and its GUI can simplify the process of including DDR macros in designs and minimize design errors. Additional considerations should be taken into account by the designer in design floorplanning and placement of I/O flip-flops to minimize datapath skew and to help improve system timing margins. Other system-related issues to consider include PLL and clock partitioning.

### Cortex-M1 Device Security

Cortex-M1-enabled devices are shipped with the following security features:

- FPGA array enabled for AES-encrypted programming and verification
- FlashROM enabled for AES-encrypted Write and Verify
- · Fusion Embedded Flash Memory enabled for AES-encrypted Write

### AES Encryption of Programming Files

Low power flash devices employ AES as part of the security mechanism that prevents invasive and noninvasive attacks. The mechanism entails encrypting the programming file with AES encryption and then passing the programming file through the AES decryption core, which is embedded in the device. The file is decrypted there, and the device is successfully programmed. The AES master key is stored in on-chip nonvolatile memory (flash). The AES master key can be preloaded into parts in a secure programming environment (such as the Microsemi In-House Programming center), and then "blank" parts can be shipped to an untrusted programming or manufacturing center for final personalization with an AES-encrypted bitstream. Late-stage product changes or personalization can be implemented easily and securely by simply sending a STAPL file with AES-encrypted data. Secure remote field updates over public networks (such as the Internet) are possible by sending and programming a STAPL file with AES-encrypted data.

The AES key protects the programming data for file transfer into the device with 128-bit AES encryption. If AES encryption is used, the AES key is stored or preprogrammed into the device. To program, you must use an AES-encrypted file, and the encryption used on the file must match the encryption key already in the device.

The AES key is protected by a FlashLock security Pass Key that is also implemented in each device. The AES key is always protected by the FlashLock Key, and the AES-encrypted file does NOT contain the FlashLock Key. This FlashLock Pass Key technology is exclusive to the Microsemi flash-based device families. FlashLock Pass Key technology can also be implemented without the AES encryption option, providing a choice of different security levels.

In essence, security features can be categorized into the following three options:

- AES encryption with FlashLock Pass Key protection
- FlashLock protection only (no AES encryption)
- No protection

Each of the above options is explained in more detail in the following sections with application examples and software implementation options.

#### Advanced Encryption Standard

The 128-bit AES standard (FIPS-192) block cipher is the NIST (National Institute of Standards and Technology) replacement for DES (Data Encryption Standard FIPS46-2). AES has been designed to protect sensitive government information well into the 21st century. It replaces the aging DES, which NIST adopted in 1977 as a Federal Information Processing Standard used by federal agencies to protect sensitive, unclassified information. The 128-bit AES standard has  $3.4 \times 10^{38}$  possible 128-bit key variants, and it has been estimated that it would take 1,000 trillion years to crack 128-bit AES cipher text using exhaustive techniques. Keys are stored (securely) in low power flash devices in nonvolatile flash memory. All programming files sent to the device can be authenticated by the part prior to programming to ensure that bad programming data is not loaded into the part that may possibly damage it. All programming verification is performed on-chip, ensuring that the contents of low power flash devices remain secure.

Microsemi has implemented the 128-bit AES (Rijndael) algorithm in low power flash devices. With this key size, there are approximately  $3.4 \times 10^{38}$  possible 128-bit keys. DES has a 56-bit key size, which provides approximately  $7.2 \times 10^{16}$  possible keys. In their AES fact sheet, the National Institute of Standards and Technology uses the following hypothetical example to illustrate the theoretical security provided by AES. If one were to assume that a computing system existed that could recover a DES key in a second, it would take that same machine approximately 149 trillion years to crack a 128-bit AES key. NIST continues to make their point by stating the universe is believed to be less than 20 billion years old.<sup>1</sup>

2. Choose the appropriate security level setting and enter a FlashLock Pass Key. The default is the **Medium** security level (Figure 12-12). Click **Next**.

If you want to select different options for the FPGA and/or FlashROM, this can be set by clicking **Custom Level**. Refer to the "Advanced Options" section on page 322 for different custom security level options and descriptions of each.

Figure 12-12 • Medium Security Level Selected for Low Power Flash Devices

#### Figure 12-18 • Security Level Set High to Reprogram Device with AES Key

Programming with this file is intended for an unsecured environment. The AES key encrypts the programming file with the same AES key already used in the device and utilizes it to program the device.

### **Reprogramming Devices**

Previously programmed devices can be reprogrammed using the steps in the "Generation of the Programming File in a Trusted Environment—Application 1" section on page 313 and "Generation of Security Header Programming File Only—Application 2" section on page 316. In the case where a FlashLock Pass Key has been programmed previously, the user must generate the new programming file with a FlashLock Pass Key that matches the one previously programmed into the device. The software will check the FlashLock Pass Key in the programming file against the FlashLock Pass Key in the device. The keys must match before the device can be unlocked to perform further programming with the new programming file.

Figure 12-10 on page 314 and Figure 12-11 on page 314 show the option **Programming previously secured device(s)**, which the user should select before proceeding. Upon going to the next step, the user will be notified that the same FlashLock Pass Key needs to be entered, as shown in Figure 12-19 on page 322.

Figure 12-19 • FlashLock Pass Key, Previously Programmed Devices

It is important to note that when the security settings need to be updated, the user also needs to select the **Security settings** check box in Step 1, as shown in Figure 12-10 on page 314 and Figure 12-11 on page 314, to modify the security settings. The user must consider the following:

- If only a new AES key is necessary, the user must re-enter the same Pass Key previously
  programmed into the device in Designer and then generate a programming file with the same
  Pass Key and a different AES key. This ensures the programming file can be used to access and
  program the device and the new AES key.
- If a new Pass Key is necessary, the user can generate a new programming file with a new Pass Key (with the same or a new AES key if desired). However, for programming, the user must first load the original programming file with the Pass Key that was previously used to unlock the device. Then the new programming file can be used to program the new security settings.

### **Advanced Options**

As mentioned, there may be applications where more complicated security settings are required. The "Custom Security Levels" section in the *FlashPro User's Guide* describes different advanced options available to aid the user in obtaining the best available security settings.